ADRIJA MUKHERJEE

ELECTRICAL AND COMPUTER ENGINEERING (M.S.)

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Education

M. S	Electrical and Electronics Engineering, University of	GPA: 3.22/4.0	2023-2025
B. Tech	Florida Electronics and Communication Engineering, Meghnad Saha Institute of Technology, MAKAUT, India	GPA: 8.56/10.0	(expected) 2017-2021 (awarded)

Skills

- Design Tools: Cadence Virtuoso, LT-SPICE, Silvaco ATLAS
- Analysis Tools: MATLAB, Verilog-A
- Relevant Coursework: Solid State Devices, VLSI-Circuits and Technology, Microfabrication Technologies, Nanodevices, Semiconductor Fabrication Technology, Future of Microelectronic Technologies, Modern Memory Devices
- Programming: C, Python, Java, VHDL, Perl
- Other: Microsoft Office 365 and English, Bengali & Hindi Languages

Projects

- Design of 4x2 SRAM circuit using Cadence Virtuoso •
- Analysis of Emerging Devices for Energy Efficient Applications
 - Designed, simulated and analyzed Logic Gates, XOR, XNOR & ADDER circuits in LT-SPICE & MATLAB.
 - The power dissipation, delay and power-delay product of the circuits were studied over different device parameter variation, temperature variation and different supply voltage in the sub-threshold regime.
- Ferroelectric Devices based Logic Circuits and Memory Design
 - Analyzed the efficacy of the Ferroelectric Devices over Conventional MOSFETs for energy-efficient digital applications.
 - Simulated sub-20nm Negative Capacitance TFET and designed 6T-SRAM using MATLAB.
- Machine Learning aided Reliability Analysis of Emerging FETs using Monte Carlo Simulations

Industry Experience

• ITC INFOTECH INDIA LTD.

Associate IT Consultant

- Ensured that personal & private data in use are in compliance with the applicable data protection rules.
- Mitigated the unauthorized acquisition of personal and private data within the organization.

• **DIRAC LAB, IIT ROORKEE**

Research Intern

- Simulated and analyzed the Logic Circuits of Ferroelectric Devices using HZO as the gate oxide.
- Analyzed the reliability issues of the Ferroelectric Devices by adjusting the different body parameters.
- Designed a Ferroelectric TFET based memory circuits using LT-SPICE.

Publications

- 1. A. Mukherjee, P. Debnath, D. Nirmal, M. Chanda, "A new analytical modelling of 10 nm negative capacitance-double gate TFET with improved cross talk and miller effects in digital circuit applications", Microelectronics Journal, Volume 133, 2023, 105689, ISSN 0026-2692, (https://doi.org/10.1016/j.mejo.2023.105689)
- 2. A. Karmakar, A. Mukherjee, S. Dhar, & M. Chanda, "A junctionless dual-gate MOSFET-based programmable inverter for secured hardware applications using nitride charge trapping", 2022 IOP Publishing Ltd (https://doi.org/10.1088/1361-6641/ac92a3)
- 3. Ghosh, S., Saha, P., Mukherjee, A. et al. "Analytical Modeling of Core-Shell Junctionless RADFET dosimeter of Improved Sensitivity", Silicon 14, 9091–9102 (2022). (https://doi.org/10.1007/s12633-022-01690-y)
- 4. A. Mukherjee, P. Debnath & M. Chanda (2023) "Machine learning-based output prediction of negative capacitance tunnel-FET", IJE, (https://doi.org/10.1080/00207217.2023.2224077)
- 5. A. Mukherjee, B. Ray, D. Das, S. Bhattacharyya, P. Debnath and M. Chanda, "Impact of Temperature on Circuit Performances of Junctionless MOSFET in Sub-threshold Regime," 2020 IEEE VLSI DEVICE CIRCUIT AND SYSTEM (VLSI DCS), 2020, pp. 1-5, (doi: 10.1109/VLSIDCS47293.2020.9179918)

Roorkee, India

August 2021 - July 2023

Kolkata, India

November 2021 – August 2022